

HSDL-4260

High-Power T-1 $\frac{3}{4}$ (5mm) AlGaAs Infrared (875nm) Lamp



Datasheet

Description

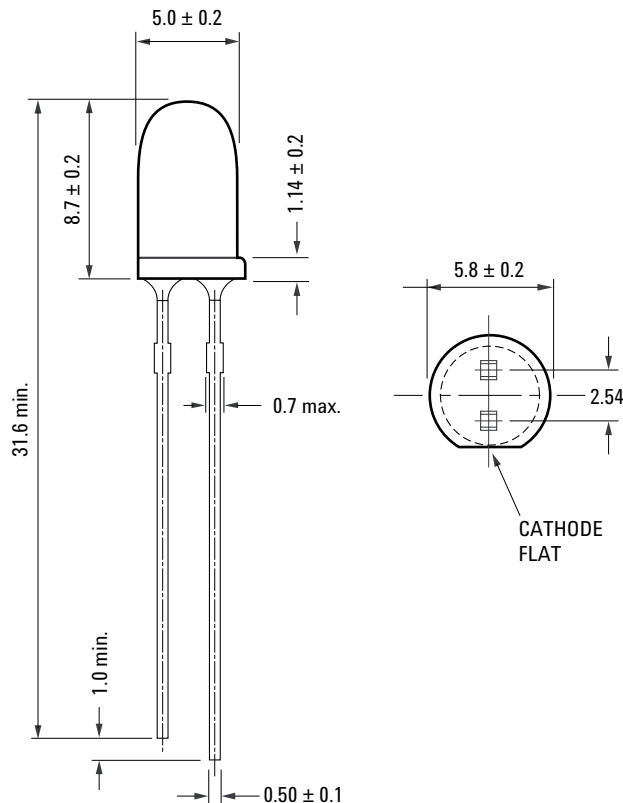
The HSDL-4260 High Power Infrared emitter was designed for applications that require high power, low forward voltage and high speed. It utilizes Aluminum Gallium Arsenide (AlGaAs) LED technology and is optimized for speed and efficiency at emission wavelengths of 875nm. The material used produces high radiant efficiency over a wide range of currents. The emitter is packaged in clear T-1 $\frac{3}{4}$ (5mm) package.

Features

- High Power AlGaAs LED Technology
- 875nm Wavelength
- T-1 $\frac{3}{4}$ Package
- Low Cost
- Low Forward Voltage: 1.4V at 20mA
- High Speed: 15ns Rise Times

Applications

- Industrial Infrared Equipments and applications
- Portable Infrared Instruments
- Consumer Electronics (Optical mouse, Infrared Remote Controllers etc)
- High Speed Infrared Communications (IR LANs, IR Modems, IR Dongles etc)



Part Number	Lead Form	Shipping Option
HSDL-4260	Straight	Bulk

Absolute Maximum Ratings at 25°C

Parameter	Symbol	Minimum	Maximum	Unit	Reference
Peak Forward Current	I_{FPK}	-	500	mA	Figure 3 Duty cycle = 20% Pulse Width = 100us
Forward Current	I_{FDC}	-	100	mA	[1]
Power Dissipation	P_{DISS}	-	230	mW	
Reverse Voltage	V_R	4	-	V	$I_R=100\mu A$
Storage Temperature	T_S	-40	100	°C	
LED Junction Temperature	T_J		110	°C	
Lead Soldering Temperature			260 for 5 sec	°C	

Notes: Derate as shown in Figure 6.

Recommended Operating Conditions

Parameter	Symbol	Min	Max	Unit	Reference
Operating Temperature	T_0	-40	85	°C	

Electrical Characteristics at 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition	Reference
Forward Voltage	V_F	-	1.4 1.7	1.9 2.3	V	$I_{FDC}=20mA$ $I_{FDC}=100mA$	Figure 2
Forward Voltage Temperature Coefficient	$\Delta V/\Delta T$	-	-1.3	-	mV/°C	$I_{FDC}=100mA$	Figure 4
Series Resistance	R_S	-	4	-	Ohms	$I_{FDC}=100mA$	
Diode Capacitance	C_0	-	70	-	pF	$V_{bias}=0V$, $f=1MHz$	
Thermal Resistance, Junction to Ambient	$R\theta_{ja}$	-	300	-	°C/W		

Optical Characteristics at 25°C

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition	Reference
Radiant On-Axis Intensity	I_E	150	200	-	mW/Sr	$I_{FDC}=100mA$	Figure 5
Radiant On-Axis Intensity Temperature Coefficient	$\Delta I_E/\Delta T$	-	-0.36	-	%/°C	$I_{FDC}=100mA$	
Viewing Angle	$2\theta_{1/2}$	-	15	-	°		Figure 7
Peak Wavelength	λ_{pk}	-	875	-	nm		Figure 1
Peak wavelength Temperature Coefficient	$\Delta\lambda/\Delta T$	-	0.2	-	nm/°C	$I_{FDC}=100mA$	
Spectral Width	$\Delta\lambda$		45	-	nm	$I_{FDC}=20mA$	Figure 1
Optical Rise and Fall Time	t_r/t_f		15	-	ns	$I_{FDC}=500mA$ Duty Ratio = 20% Pulse Width=100ns	

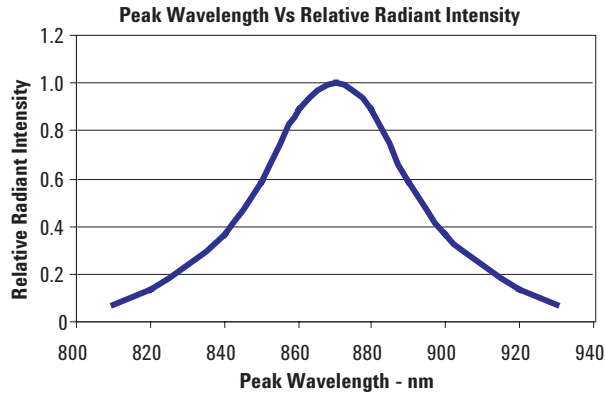


Figure 1. Relative Radiant Intensity vs. Wavelength

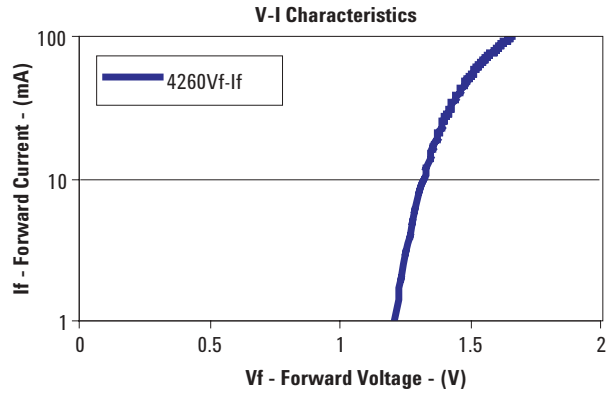


Figure 2. DC Forward Current vs. Forward Voltage

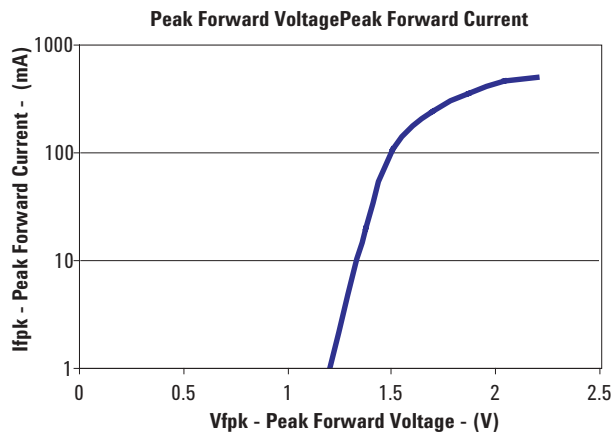


Figure 3. Peak Forward Current vs. Forward Voltage

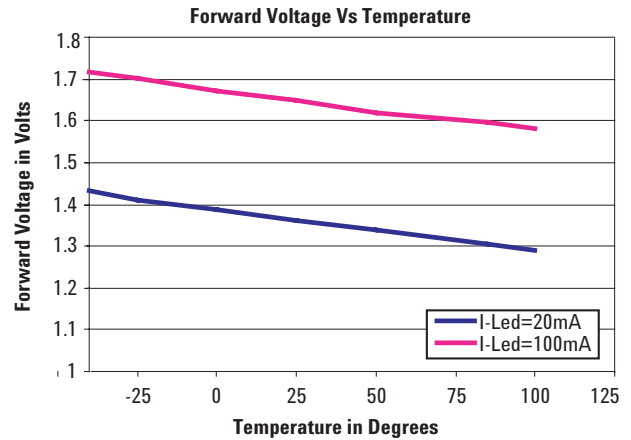


Figure 4. Forward Voltage vs. Ambient Temperature

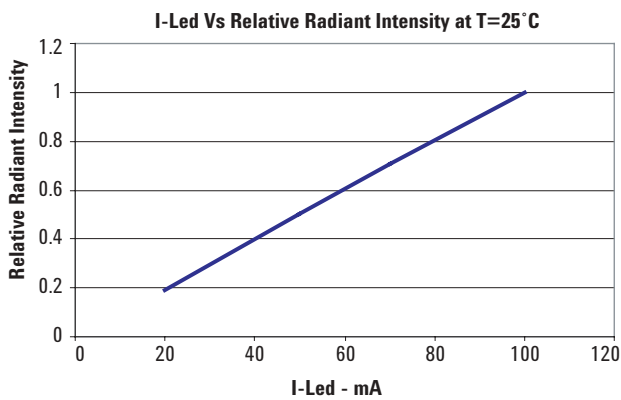


Figure 5. Relative Radiant Intensity vs. DC Forward Current

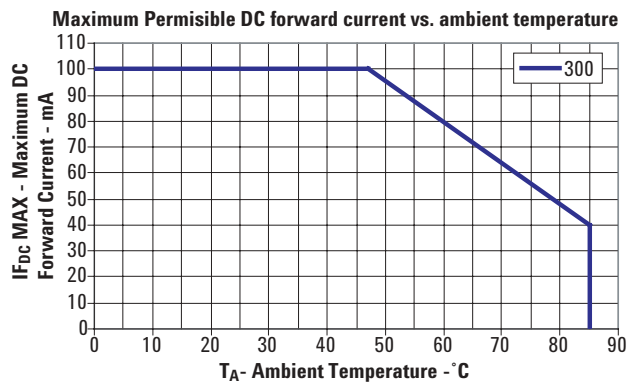


Figure 6. DC Forward Current vs. Ambient Temperature Derated Based on $T_{JMAX}=110^{\circ}C$

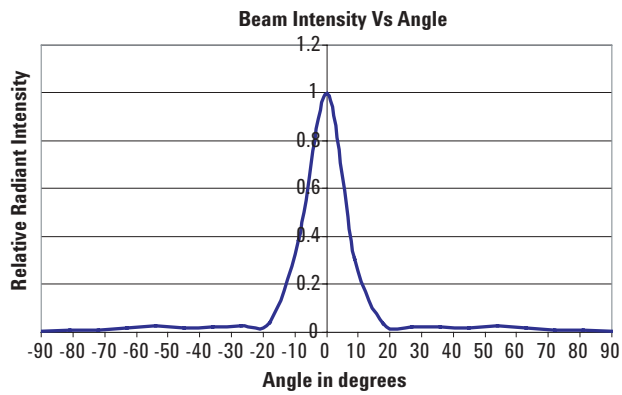
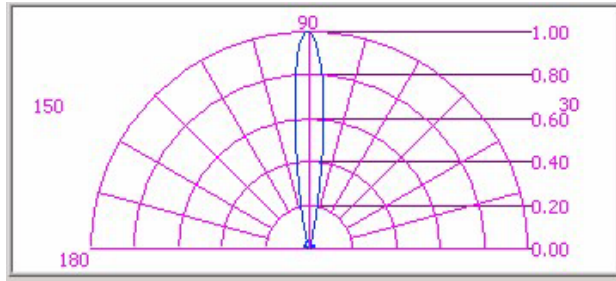


Figure 7. Radiant Intensity vs. Angular Displacement for HSDL-4260

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